

# 1N60PW, 1N60SW

## Schottky Barrier Diode

### Features

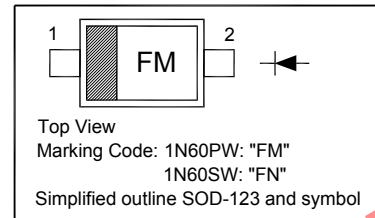
- High reliability
- Low forward voltage and reverse current

### Applications

- For electronic calculator, etc.
- Low current rectification and high speed switching

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



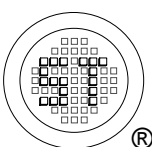
### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	10	V
Peak Forward Current	$I_{FM}$	150	mA
Average Rectified Output Current	$I_O$	50	mA
Surge Forward Current	$I_{surge}$	500	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

### Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	$I_F$	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	$I_R$	-	50 100	$\mu\text{A}$
Reverse Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_R$	45	-	V
Junction Capacitance at $f = 1\text{ MHz}$ , $V = -1\text{ V}$	$C_j$	-	1	pF
Rectification efficiency at $V_i = 2\text{ V}_{rms}$ , $R = 5\text{ K}\Omega$ , $C = 20\text{ pF}$ , $f = 40\text{ MHz}$	$\eta$	55	-	%

Pair  $\Delta I_F \leq 6\text{ mA}$  at  $1\text{ V}$ ,  $\Delta I_R \leq 20\text{ }\mu\text{A}$  at  $10\text{ V}$



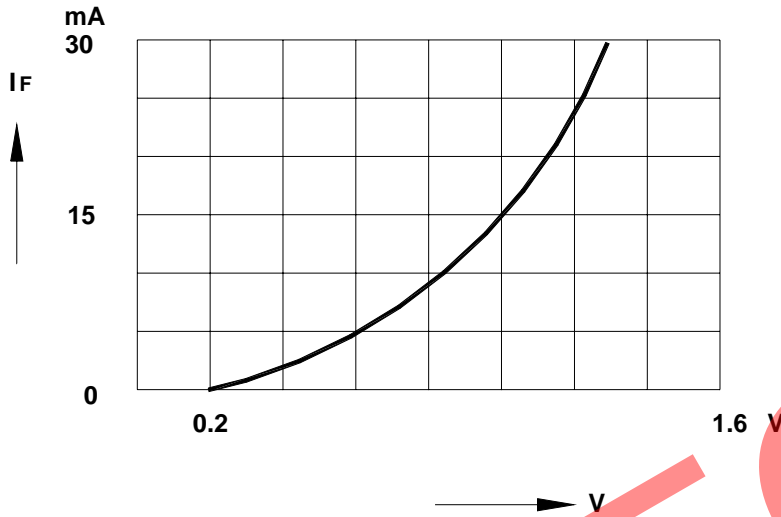
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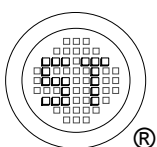
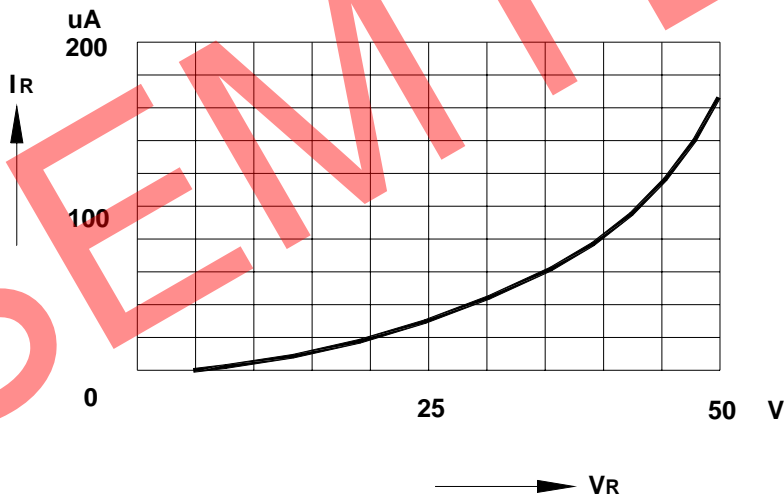
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### Forward Characteristics



### Reverse Characteristics



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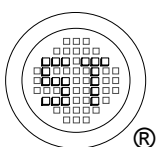
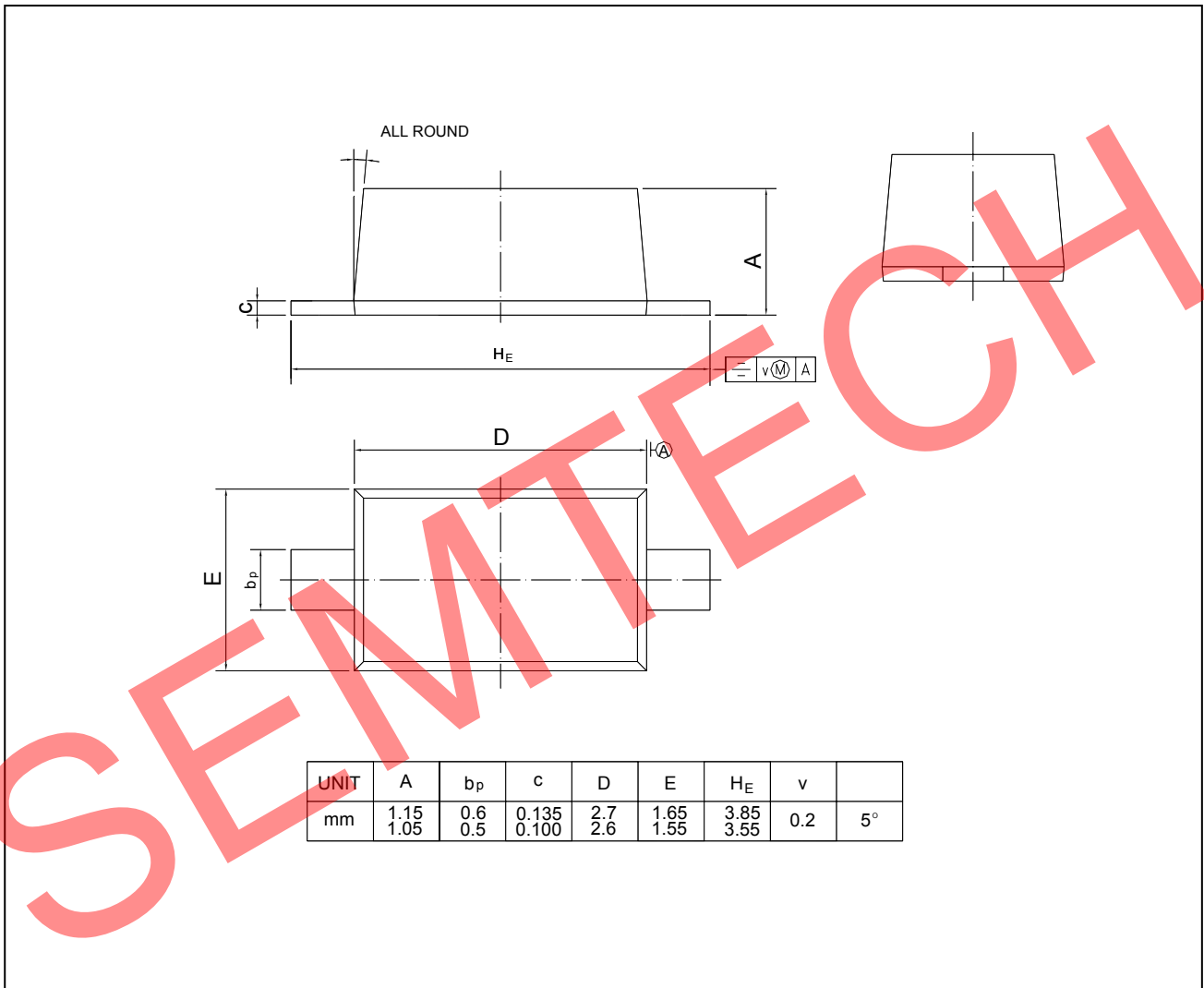
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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



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